

RECTRON
SEMICONDUCTOR
TECHNICAL SPECIFICATION

BAT54C

DUAL SURFACE MOUNT SCHOTTKY

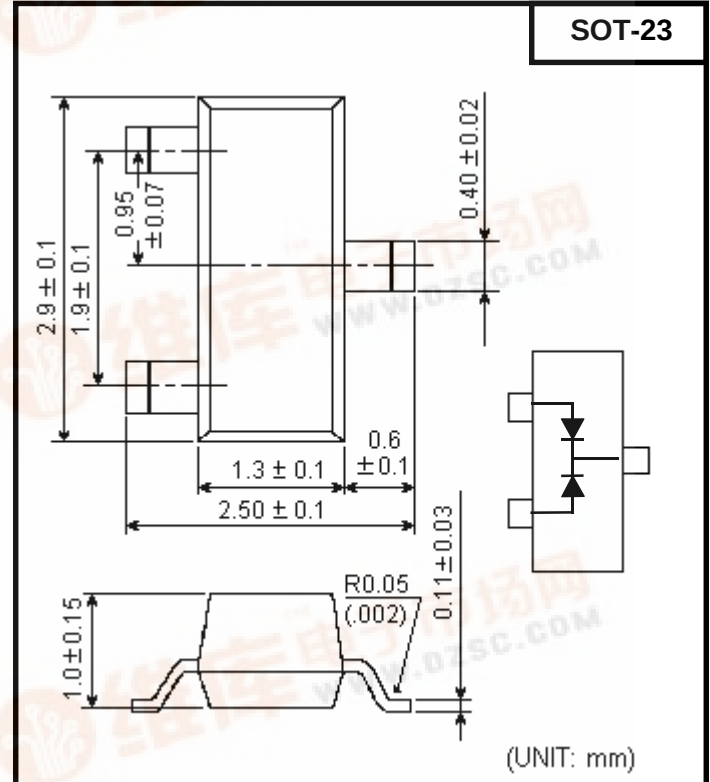
Absolute Maximum Ratings per Diode (Ta=25°C)

Items	Symbol	Ratings	Unit
Reverse Voltage	VR	30	V
Power Dissipation *	P _{TOT}	300	mW
Forward Voltage @ If = 100mA	VF	1.0	V
Forward Current	IF	200	mA
Junction Temp.	T _j	-55 to 125	°C
Storage Temp.	T _{STG}	-55 to 150	°C

Mechanical Data

Items	Materials
Package	SOT-23
Lead Frame	42 Alloy
Lead Finish	Solder Plating
Bond Wire	Au
Mold Resin	Epoxy
Chip	Silicon

Dimensions



Electrical Characteristics per diode (Ta=25°C)

Ratings	Symbol	Ratings	Unit
Minimum Repetitive Peak Reverse Voltage	VRRM	30	V
Maximum Repetitive Peak Forward Current	IFRM	300	mA
Maximum Forward Voltage IF= 100uA IF= 1mA IF= 10mA IF= 30mA IF= 100mA	VF	240 320 400 500 1000	mV
Maximum Reverse Current VR= 25V	IR	2.0	uA
Maximum Junction Capacitance VR= 1V, f= 1MHz	Cj	15	pF
Maximum Reverse Recovery Time IF= 10mA, IR= 10mA, IRR= 1mA, RL= 100W	trr	5	ns
Thermal Resistance*	Rθjc	430	°C/W

(Mounted on a 10x8x0.6mm ceramic substrate)